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FORM PTO-1449
(REV. 7-80)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
51889/2 USAPPLICATION NO.
10/613,169

INFORMATION DISCLOSURE CITATION

Title: **MULTI-CONFIGURABLE INDEPENDENTLY
MULTI-GATED MOSFET**

APPLICANT - Douglas R. Hackler, Sr. et al.

FILING DATE-
July 3, 2003

U.S. PATENT DOCUMENTS

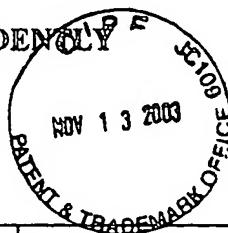
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
PC	1	2002/0187610 A1	12/12/02	Furukawa et al.	438	283	06/12/01
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PC	17	5,349,228	09/20/94	Neudeck et al.	257	365	12/07/93
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PC	19	3,755,012	08/28/73	George et al.	148	175	03/19/71

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	20							
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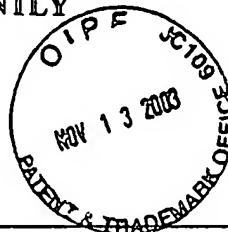
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PC	47	Narasimha et al., "High Performance Sub-40nm CMOS Devices on SOI for the 70nm Technology Node," IBM Microelectronics Semiconductor Research and Development Center (SRDC), Hopewell Junction, NY 12533, USA, pgs. 29.2.1-29.2.4.
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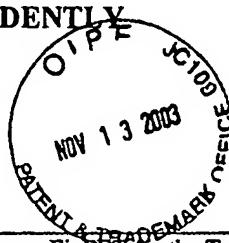
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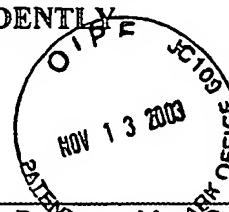
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PC	92	Yahishita et al., "High Performance Damascene Metal Gate MOSFET's for 0.1 μ m Regime," IEEE Transactions on Electron Devices, Vol. 47, No. 5, May 2000, pgs. 1028-1034.
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